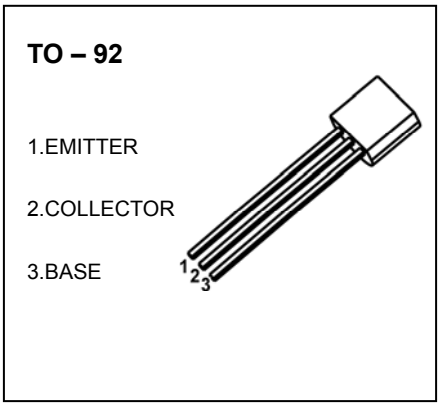
TO-92 Plastic-Encapsulate Transistors

STA124 TRANSISTOR (PNP)



FEATURES

- Suitable For low Voltage Large Current Drivers
- High DC Current Gain and Large Current Capability
- Complementary Pair with STC128

Maximum Ratings (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-15	V
V_{CEO}	Collector-Emitter Voltage	-12	V
V_{EBO}	Emitter-Base Voltage	-6.5	V
I_C	Collector Current	-1	A
P_C	Collector Power Dissipation	625	mW
$R_{\Theta JA}$	Thermal Resistance From Junction To Ambient	200	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-50μA, I_E=0	-15			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-12			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-50μA, I_C=0	-6.5			V
Collector cut-off current	I_{CBO}	V_{CB}=-15V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V, I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-1V, I_C=-100mA	200		450	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA			-0.4	V
Transition frequency	f_T	V_{CE}=-5V,I_C=-50mA		260		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		5		pF